Figures



Fig.1: XPS data showing the reduction of Ga_xO_y species following TMA pretreatment prior to thermal Al₂O₃ ALD.



Fig.2: D_{IT} analysis from quasi-static C-V measurements show a decrease of defect densities in GaN MOSCAPs following the reduction of the Ga_xO_y native oxide layer.



Fig.3: AFM images and RMS surface roughness for (a) GaN coated by Al₂O₃ ALD with no pretreatment and (b) GaN exposed to TMA prior to Al₂O₃ ALD.

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